

# MITSUBISHI RF POWER TRANSISTOR 2SC2086

## NPN EPITAXIAL PLANAR TYPE

### DESCRIPTION

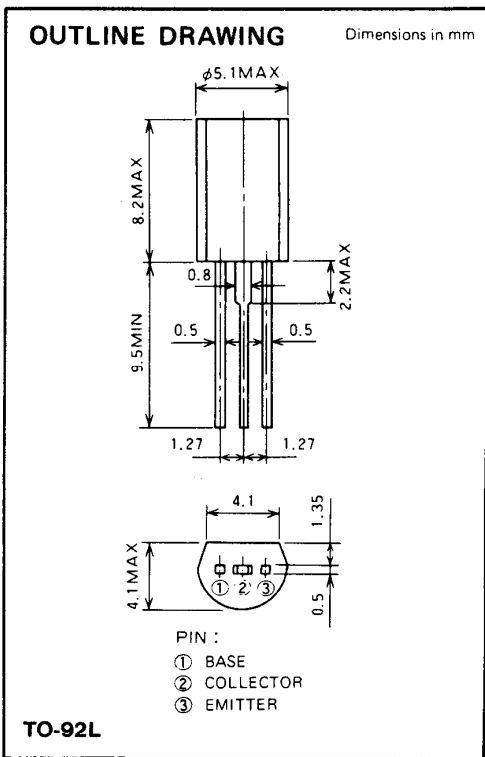
2SC2086 is a silicon NPN epitaxial planar type transistor designed for RF power amplifiers in HF band mobile radio applications.

### FEATURES

- High power gain:  $G_{pe} \geq 13\text{dB}$   
@  $V_{CC} = 12\text{V}$ ,  $P_O = 0.3\text{W}$ ,  $f = 27\text{MHz}$
- Emitter ballasted construction, gold metallization for good performances.
- TO-92 similar package with low thermal resistance.

### APPLICATION

Driver amplifiers in general in HF band mobile radio applications.



### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CBO}$	Collector to base voltage		75	V
$V_{EBO}$	Emitter to base voltage		4	V
$V_{CEO}$	Collector to emitter voltage	$R_{BE} = \infty$	35	V
$I_C$	Collector current		1	A
$P_C$	Collector dissipation	$T_a = 25^\circ\text{C}$	0.8	W
$T_j$	Junction temperature		135	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55 to 135	$^\circ\text{C}$
$R_{th-a}$	Thermal resistance	Junction to ambient	137.5	$^\circ\text{C}/\text{W}$

Note. Above parameters are guaranteed independently.

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 1\text{mA}$ , $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 1\text{mA}$ , $I_E = 0$	75			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 10\text{mA}$ , $R_{BE} = \infty$	35			V
$I_{CBO}$	Collector cutoff current	$V_{CB} = 30\text{V}$ , $I_E = 0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter cutoff current	$V_{EB} = 3\text{V}$ , $I_C = 0$			100	$\mu\text{A}$
$h_{FE}$	DC forward current gain*	$V_{CE} = 10\text{V}$ , $I_C = 0.1\text{A}$	35	70	300	—
$P_O$	Output power	$V_{CC} = 12\text{V}$ , $P_{in} = 15\text{mW}$ , $f = 27\text{MHz}$	0.3	0.45		W
$\eta_C$	Collector efficiency		50	60		%

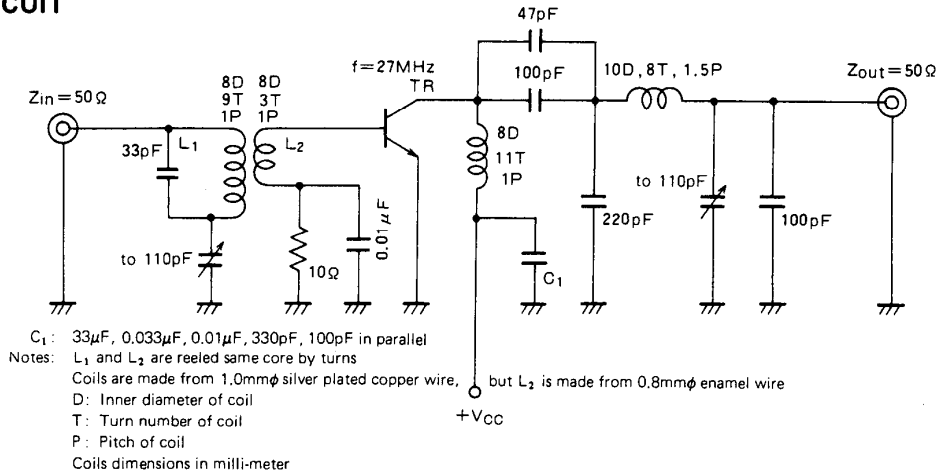
Note. \*Pulse test,  $P_W = 150\mu\text{s}$ , duty=5%.

Above parameters, ratings, limits and conditions are subject to change.

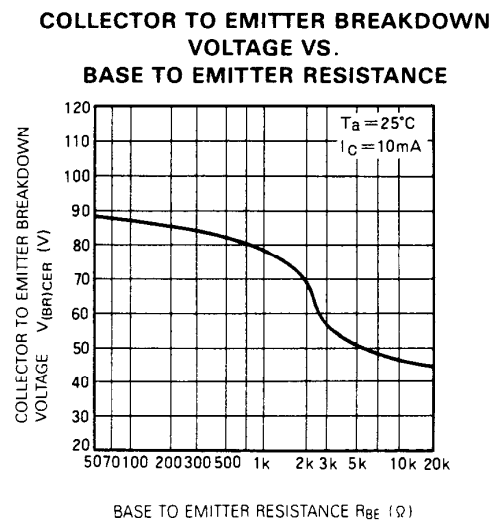
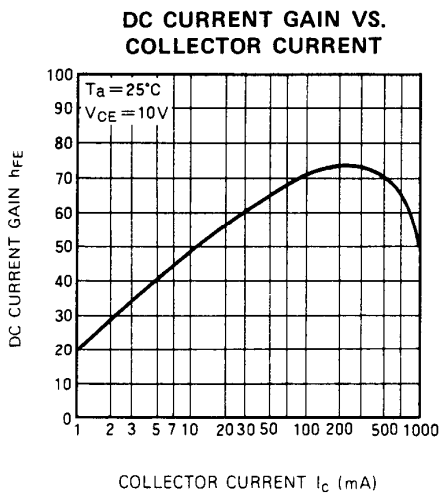
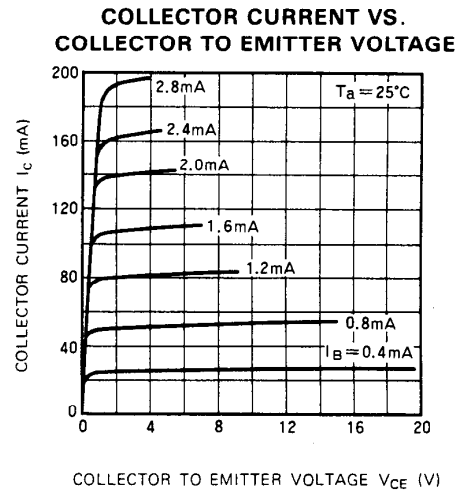
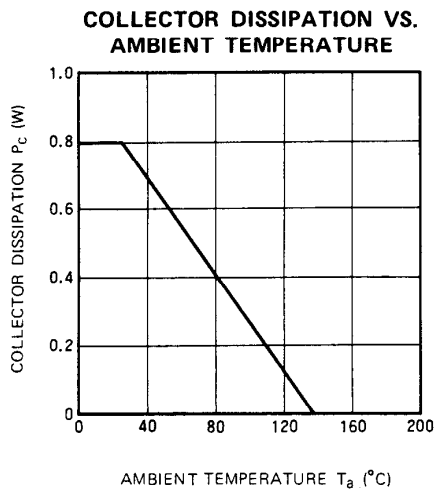
NOV. '97



**TEST CIRCUIT**

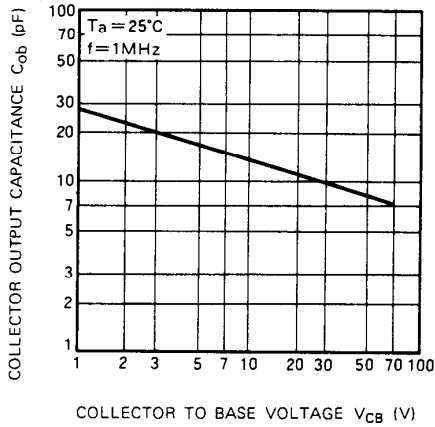


**TYPICAL PERFORMANCE DATA**

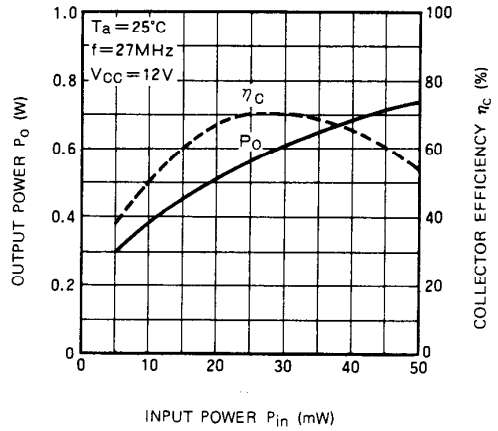


**NPN EPITAXIAL PLANAR TYPE**

**COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE**



**OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER**



**OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE**

